



#### 100V NPN HIGH PERFORMANCE TRANSISTOR IN PowerDI3333-8

#### **Features**

- $BV_{CEO} > 100V$
- Small Form Factor Thermally Efficient Package. Enables Higher **Density End Products**
- I<sub>C</sub> = 2A High Continuous Current
- I<sub>CM</sub> = 6A Peak Pulse Current
- Low Saturation Voltage V<sub>CE(SAT)</sub> < 250mV @ 1A
- Complementary PNP Type: DXTP07100BFG
- Rated to +175°C-Ideal for High Temperature Environment
- Wettable Flank for Improved Optical Inspection
- Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)

## **Mechanical Data**

- Case: PowerDI®3333-8
- Case Material: Molded Plastic. "Green" Molding Compound. UL Flammability Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish Matte Tin Solderable per MIL-STD-202, Method 208 @3
- Weight: 0.03 grams (Approximate)

### **Applications**

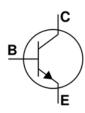
- Load Switch
- Linear Regulator
- MOSFET or IGBT Gate Driving

PowerDI3333-8 (SWP) (Type UX)





**Equivalent Circuit** 



Device Symbol

### **Ordering Information** (Note 4)

Part Number	Marking	Reel Size (inches)	Tape Width (mm)	Quantity per Reel
DXTN07100BFG-7	2H7	7	12	2,000

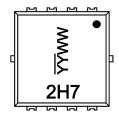
Notes: 1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant.

**Bottom View** 

- 2. See https://www.diodes.com/quality/lead-free/ for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
- 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
- 4. For packaging details, go to our website at https://www.diodes.com/design/support/packaging/diodes-packaging/

# **Marking Information**

PowerDI3333-8 (SWP) (Type UX)



2H7 = Product Type Marking Code YYWW = Date Code Marking YY = Last Two Digits of Year (ex: 18 = 2018) WW = Week Code (01 to 53)



# Absolute Maximum Ratings (@TA = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit
Collector-Base Voltage	V <sub>CBO</sub>	120	V
Collector-Emitter Voltage	V <sub>CEO</sub>	100	V
Emitter-Base Voltage	V <sub>EBO</sub>	7	V
Continuous Collector Current	Ic	2	Α
Peak Pulse Current	I <sub>CM</sub>	6	Α

# Thermal Characteristics ( $@T_A = +25^{\circ}C$ , unless otherwise specified.)

Characteristic	Symbol	Value	Unit	
	(Note 5)		0.9	W
Power Dissipation	(Note 6)	PD	2.1	W
	(Note 7)		3.1	W
	(Note 5)		140	°C/W
Thermal Resistance, Junction to Ambient	(Note 6)	$R_{\theta JA}$	65	°C/W
	(Note 7)		44	°C/W
Thermal Resistance, Junction to Leads (Note 8	$R_{ heta JL}$	8.5	°C/W	
Operating and Storage Temperature Range	T <sub>J</sub> , T <sub>STG</sub>	-55 to +175	°C	

### ESD Ratings (Note 9)

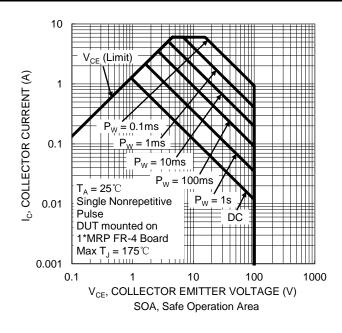
Characteristic	Symbol	Value	Unit	JEDEC Class
Electrostatic Discharge—Human Body Model	ESD HBM	4000	V	3A
Electrostatic Discharge—Machine Model	ESD MM	400	V	С

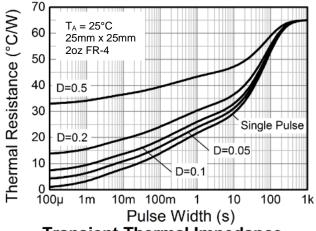
#### Notes:

- 5. For a device mounted with the collector tab on MRP FR4-PCB; device is measured under still air conditions whilst operating in a steady-state.
- 6. Same as Note 5, except the device is mounted on 25mm  $\times$  25mm 2oz copper.
- 7. Same as Note 5, except the device is mounted on 50mm  $\times$  50mm 2oz copper.
- 8. Thermal resistance from junction to solder-point (at the collector tab).
- 9. Refer to JEDEC specification JESD22-A114 and JESD22-A115.

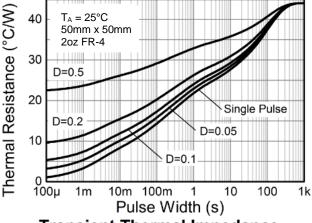


## **Thermal Characteristics and Derating Information**

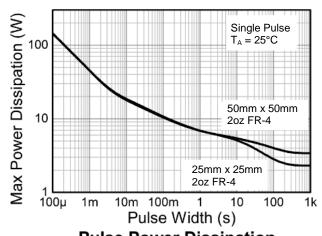




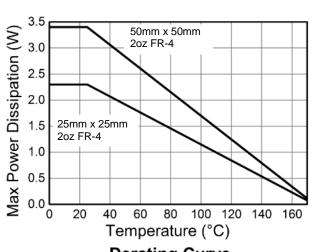




**Transient Thermal Impedance** 



**Pulse Power Dissipation** 



**Derating Curve** 



## **Electrical Characteristics** (@T<sub>A</sub> = +25°C, unless otherwise specified.)

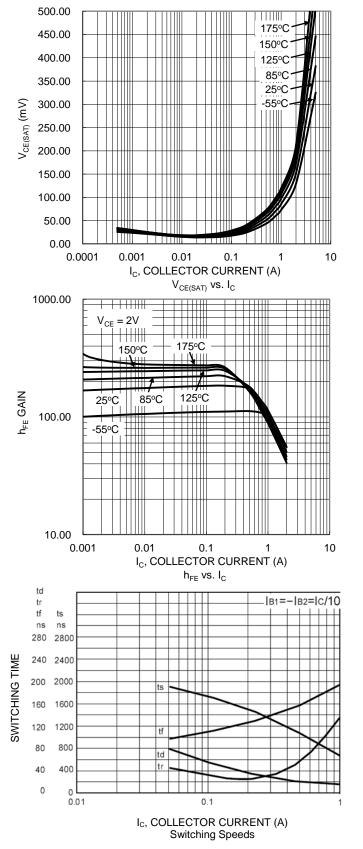
Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition
Collector-Base Breakdown Voltage	BV <sub>CBO</sub>	120	264	_	V	$I_{C} = 100 \mu A$
Collector-Emitter Breakdown Voltage (Note 10)	BV <sub>CEO</sub>	100	129	_	V	I <sub>C</sub> = 10mA
Emitter-Base Breakdown Voltage	BV <sub>EBO</sub>	7	8.4	_	V	I <sub>E</sub> = 100μA
Collector Cut-Off Current		_	_	50	nA	V <sub>CB</sub> = 100V
Collector Cut-On Current	I <sub>CBO</sub>	_	_	10	μA	V <sub>CB</sub> = 100V, T <sub>A</sub> = +125°C
Emitter Cut-Off Current	I <sub>EBO</sub>	_	_	20	nA	V <sub>EB</sub> = 6V
Callegtor Emitter Caturation Voltage (Note 10)	V	_	90	250	mV	$I_C = 1A$ , $I_B = 100mA$
Collector-Emitter Saturation Voltage (Note 10)	V <sub>CE</sub> (SAT)	_	150	400	mV	$I_C = 2A$ , $I_B = 200mA$
Base-Emitter Saturation Voltage (Note 10)	V <sub>BE(SAT)</sub>	_	0.86	1	V	I <sub>C</sub> = 1A, I <sub>B</sub> = 100mA
Base-Emitter Turn-On Voltage (Note 10)	V <sub>BE(ON)</sub>	_	0.79	0.95	V	I <sub>C</sub> = 1A, V <sub>CE</sub> = 2V
		70	183	_	_	I <sub>C</sub> = 50mA, V <sub>CE</sub> = 2V
DC Current Gain (Note 10)	h <sub>FE</sub>	100	172	300	_	I <sub>C</sub> = 500mA, V <sub>CE</sub> = 2V
DC Current Gain (Note 10)		55	113	_	_	$I_C = 1A$ , $V_{CE} = 2V$
		25	56	_	_	$I_C = 2A$ , $V_{CE} = 2V$
Current Gain-Bandwidth Product	f⊤	140	175	_	MHz	$V_{CE} = 5V, I_{C} = 100mA,$ f = 100MHz
Switching Time	t <sub>ON</sub>	_	80	_	ns	I <sub>C</sub> = 500mA, V <sub>CC</sub> = 10V,
Switching Time	t <sub>OFF</sub>	_	1200	_	ns	$I_{B1} = -I_{B2} = 50 \text{mA}$
Output Capacitance	Сово	_	_	30	pF	V <sub>CB</sub> = 10V, f = 1MHz

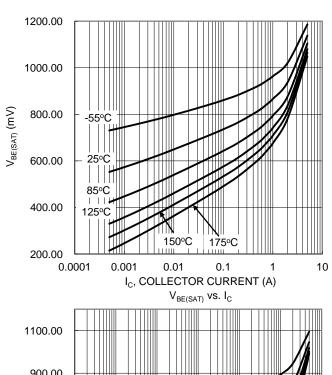
Note:

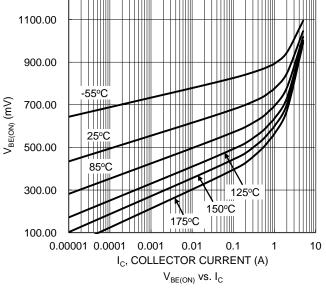
10. Measured under pulsed conditions. Pulse width  $\leq$  300µs. Duty cycle  $\leq$  2%.



# $\textbf{Typical Electrical Characteristics} \ (@T_{A} = +25^{\circ}C, \ unless \ otherwise \ specified.)$





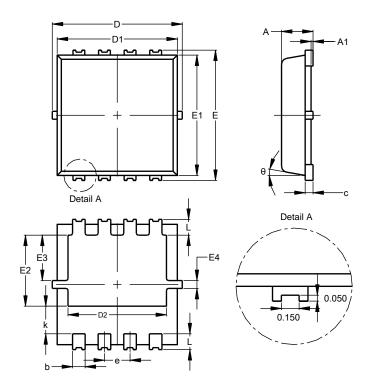




# **Package Outline Dimensions**

Please see http://www.diodes.com/package-outlines.html for the latest version.

#### PowerDI3333-8 (SWP) (Type UX)

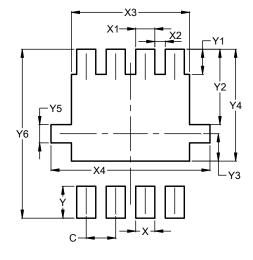


PowerDI3333-8 (SWP)				
(Type UX)				
Dim	Min	Max	Тур	
Α	0.75	0.85	0.80	
A1	0.00	0.05		
b	0.25	0.40	0.32	
С	0.10	0.25	0.15	
D	3.20	3.40	3.30	
D1	2.95	3.15	3.05	
D2	2.30	2.70	2.50	
Е	3.20	3.40	3.30	
E1	2.95	3.15	3.05	
E2	1.60	2.00	1.80	
E3	0.95	1.35	1.15	
E4	0.10	0.30	0.20	
е			0.65	
k	0.50	0.90	0.70	
L	0.30	0.50	0.40	
θ	0°	12°	10°	
All Dimensions in mm				

## **Suggested Pad Layout**

Please see http://www.diodes.com/package-outlines.html for the latest version.

#### PowerDI3333-8 (SWP) (Type UX)



Dimensions	Value (in mm)
С	0.650
X	0.420
X1	0.420
X2	0.230
Х3	2.600
X4	3.500
Υ	0.700
Y1	0.550
Y2	1.650
Y3	0.600
Y4	2.450
Y5	0.400
Y6	3.700

Note: For high voltage applications, the appropriate industry sector guidelines should be considered with regards to creepage and clearance distances between device terminals and PCB tracking.



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